

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	10/077,817	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/26 22:47
L3	859	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:50
L4	115	((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and DRAM) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:48
L5	566	((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))) and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:51
L6	2430	(((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) and (1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:51
L7	859	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:50
L8	121	((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor)) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:51
L9	121	(((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) and ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:51

L10	121	(((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) and ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:51
L11	102	(((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor)) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))) and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 22:51
S1	214	PLED	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 13:47
S2	0	PLED and ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 13:47
S3	79	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 14:15
S4	1277	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:18
S5	518	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 14:16
S6	1674	(((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) not ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and ferroelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 14:17

S7	1674	(((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) not ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and ferroelectric)) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 14:18
S8	65	((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and DRAM) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 14:18
S9	79	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 14:22
S10	65	((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))) and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 16:02
S11	431	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 16:01
S12	443	(1T/1C) (1T-1C) (1T1C) (one adj5 transistor adj5 one adj5 capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 16:04

S13	431	((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 16:03
S14	444	(1T/1C) (1T-1C) (1T1C) (one adj5 transistor adj5 one adj5 capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 16:04
S15	1700	((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 16:08
S16	1804	1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 16:08
S17	79	((((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) and (1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:10
S18	1333	((data information) near3 (hold\$3 retain\$3)) near3 mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:12
S19	26187	((((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:17
S20	2044	((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:17
S21	188	((((data information) near3 (hold\$3 retain\$3)) near3 mode) and (((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:18

S22	1806	1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:19
S23	1	(((((data information) near3 (hold\$3 retain\$3)) near3 mode) same (((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative))) and (1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 12:42
S24	3	((1T/1C 1T1C (one near4 transistor near4 one near4 capacitor))) and PLED	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 14:44
S25	14	(((((data information) near3 (hold\$3 retain\$3)) near3 mode) same (((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/16 14:44
S48	682	PLED	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S49	1	PLED and ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S50	859	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S51	2150	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S52	1085	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16

S53	2348	(((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) not ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and ferroelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S54	2348	(((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) not ((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and ferroelectric)) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S55	115	(((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and DRAM) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S56	859	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S57	566	(((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))) and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S58	859	(1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S59	880	(1T/1C) (1T-1C) (1T1C) (one adj5 transistor adj5 one adj5 capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16

S60	859	((1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor) and (((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S61	881	(1T/1C) (1T-1C) (1T1C) (one adj5 transistor adj5 one adj5 capacitor) and (((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S62	2404	((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S63	2573	1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S64	2430	((((read\$3/writ\$3) read\$3 writ\$3) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss)) and (1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S65	1803	((data information) near3 (hold\$3 retain\$3)) near3 mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S66	33160	((((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S67	2855	((read\$3/writ\$3) (writ\$3/read\$3) read\$3 writ\$3 program\$4) with ((word address) adj2 line) with (voltage potential bias) with (ground negative Vss Vbb)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S68	271	((((data information) near3 (hold\$3 retain\$3)) near3 mode) and (((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16

S69	2573	1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S70	2414	(((data information) near3 (hold\$3 retain\$3)) near3 mode) same (((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative))) and (1T/1C) (1T-1C) (1T1C) (one adj transistor adj one adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S71	9	((1T/1C 1T1C (one near4 transistor near4 one near4 capacitor))) and PLED	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S72	19	(((data information) near3 (hold\$3 retain\$3)) near3 mode) same (((word address) near2 line) gate) near4 (potential voltage bias) with (ground Vss Vbb negative))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:16
S74	2	10/077,817	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 16:26